## Abstract of the Disclosure

A method for forming a metal interconnect comprises exposing a dielectric layer to an etch chemistry containing nitrogen-containing compound such as  $NH_3$ ,  $NF_3$  or  $N_2O$ . The nitrogen-containing compound provides selectivity and/or profile control comparable to that provided by  $N_2$ , while avoiding poisoning of photoresist by embedded  $N_2$ .